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Team Nexperia



1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier in common cathode configuration with an integrated guard ring for stress protection, encapsulated in an ultra thin DFN2020D-3 (SOT1061D) leadless small Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

2. Features and benefits

- Average forward current I_{F(AV)} ≤ 1 A
- Reverse voltage $V_R \le 40 \text{ V}$
- Low forward voltage $V_F \le 500 \text{ mV}$
- Low reverse current
- Reduced Printed-Circuit-Board (PCB) area requirements
- Exposed heat sink (cathode pad) for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with visible and solderable side pads
- Suitable for Automatic Optical Inspection (AOI) of solder joints
- AEC-Q101 qualified

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Free-wheeling application
- Reverse polarity protection
- Low power consumption application
- Battery chargers for mobile equipment
- LED backlight for mobile application

4. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per diode							
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; T _{amb} ≤ 110 °C; square wave	[1]	-	-	1	A
		δ = 0.5 ; f = 20 kHz; T _{sp} ≤ 140 °C; square wave		-	-	1	A





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40 V, 1 A low VF dual MEGA Schottky barrier rectifier

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _R	reverse voltage	T _j = 25 °C	-	-	40	V
Per diode						,
V _F	forward voltage	I _F = 1 A; t _p ≤ 300 μs; δ ≤ 0.02 ; T _j = 25 °C; pulsed	-	440	500	mV
I _R	reverse current	$\label{eq:VR} \begin{array}{l} V_{R} = 40 \; V; \; t_{p} \leq 300 \; \mu s; \; \delta \leq 0.02 \; \; ; \\ T_{j} = 25 \; ^{\circ}C; \; pulsed \end{array}$	-	12	55	μA

[1] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	anode diode 1	A1	3	3
2	anode diode 2	A2		
3	common cathode	к	1 2 Transparent top view DFN2020D-3 (SOT1061D)	1 2 006aaa438

6. Ordering information

Table 3. Ordering in	formation					
Type number	Package					
	Name	Description	Version			
PMEG4010CPAS	DFN2020D-3	DFN2020D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 x 2 x 0.65 mm	SOT1061D			

7. Marking

Table 4. Marking codes	
Type number	Marking code
PMEG4010CPAS	CU

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per diode		·				
V _R	reverse voltage	T _j = 25 °C		-	40	V
I _F	forward current	T _{sp} ≤ 130 °C; δ = 1		-	1.4	А
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; T _{amb} ≤ 110 °C; square wave	[1]	-	1	A
		δ = 0.5 ; f = 20 kHz; T _{sp} ≤ 140 °C; square wave		-	1	A
I _{FRM}	repetitive peak forward current	t _p ≤ 1 ms; δ ≤ 0.25		-	7	А
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	9	A
Per device;	one diode loaded	·	-1			
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	500	mW
			[3]	-	960	mW
			[1]	-	1800	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

40 V, 1 A low VF dual MEGA Schottky barrier rectifier

9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per device; one diode loaded							
fi	thermal resistance from junction to ambient	in free air	n free air [1][2]	-	-	250	K/W
			[1][3]	-	-	130	K/W
			[1][4]	-	-	70	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	12	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of cathode tab.

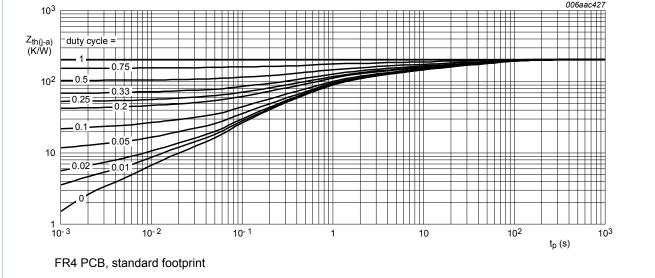
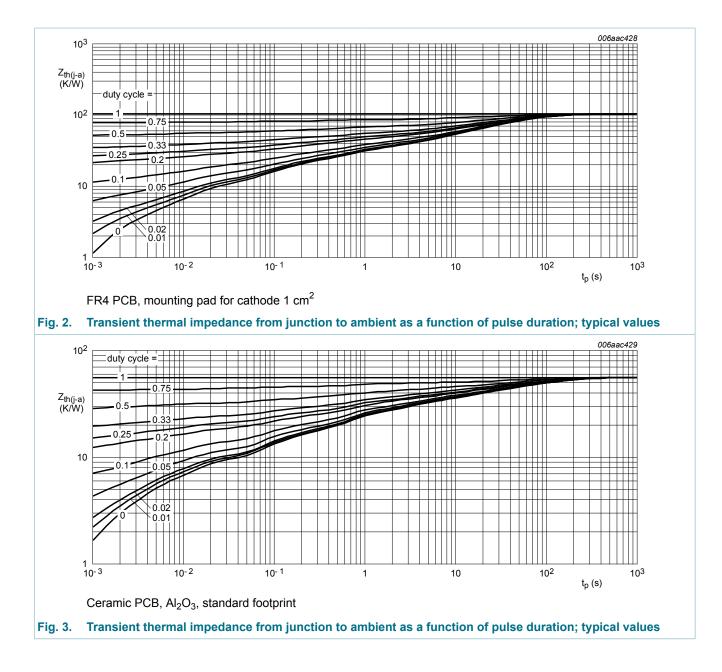


Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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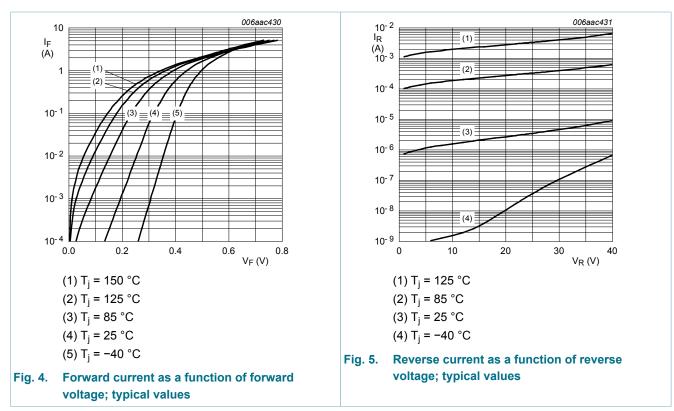
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per diode						
V _{(BR)R}	reverse breakdown voltage	$I_R = 1 \text{ mA; } t_p = 300 \mu\text{s}; \delta = 0.02 ; \\ T_j = 25 ^\circ\text{C}; \text{ pulsed}$	40	-	-	V
V _F forward v	forward voltage	$I_F = 100 \text{ mA}; t_p \le 300 \mu\text{s}; \delta \le 0.02 \hspace{0.2cm} ; \label{eq:IF}$ $T_j = 25 \ ^\circ\text{C}; \text{ pulsed}$	-	320	-	mV
		$I_F = 1 \text{ A}; t_p \le 300 \mu\text{s}; \delta \le 0.02 ;$ $T_j = 25 \text{ °C}; \text{ pulsed}$	-	440	500	mV
I _R reve	reverse current	$\label{eq:VR} \begin{split} V_{R} &= 10 \; V; \; t_{p} \leq 300 \; \mu s; \; \overline{o} \leq 0.02 \; \; ; \\ T_{j} &= 25 \; ^{\circ} \mathrm{C}; \; pulsed \end{split}$	-	2.5	-	μA
		$\label{eq:VR} \begin{split} V_{R} &= 40 \text{ V}; \ t_{p} \leq 300 \ \mu\text{s}; \ \delta \leq 0.02 \ ; \\ T_{j} &= 25 \ ^{\circ}\text{C}; \ \text{pulsed} \end{split}$	-	12	55	μA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	130	-	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	50	-	pF
t _{rr}	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{R(meas)} = 0.25 \text{ A};$ $T_j = 25 \text{ °C}$	-	3.5	-	ns



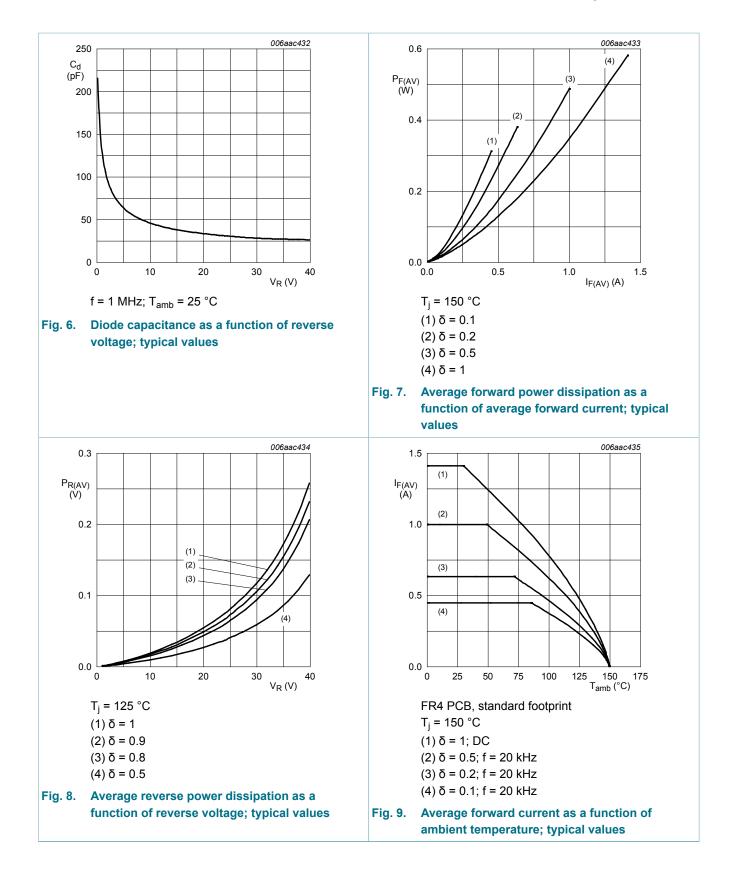
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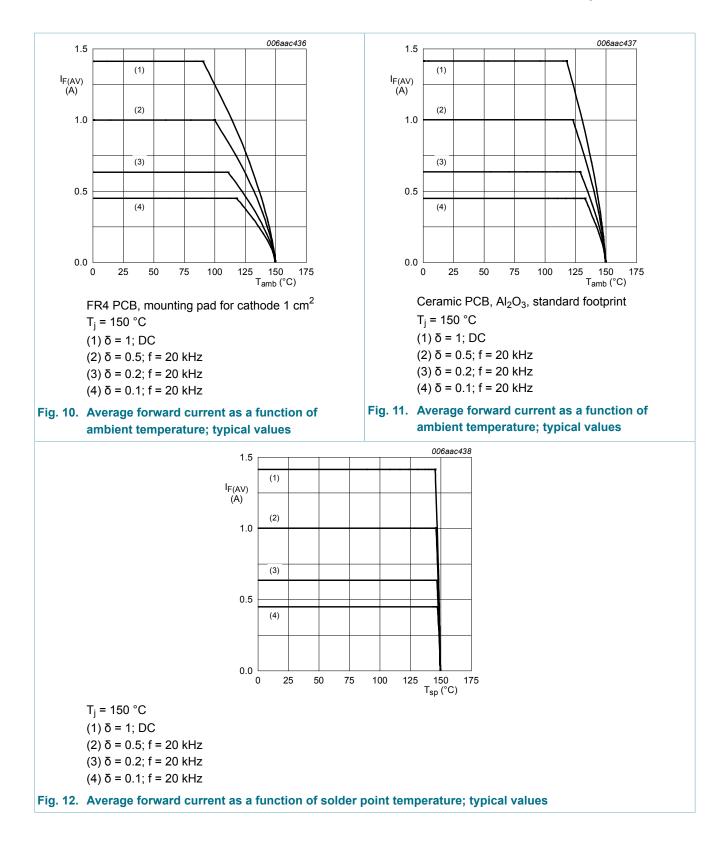
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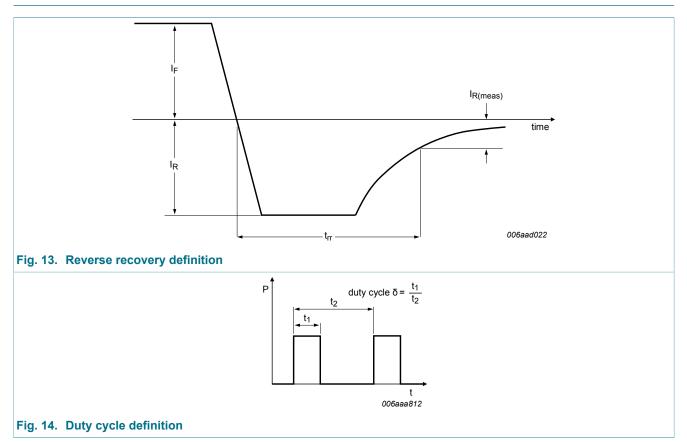


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11. Test information



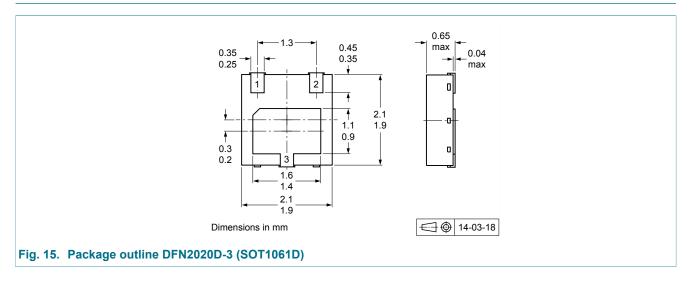
The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

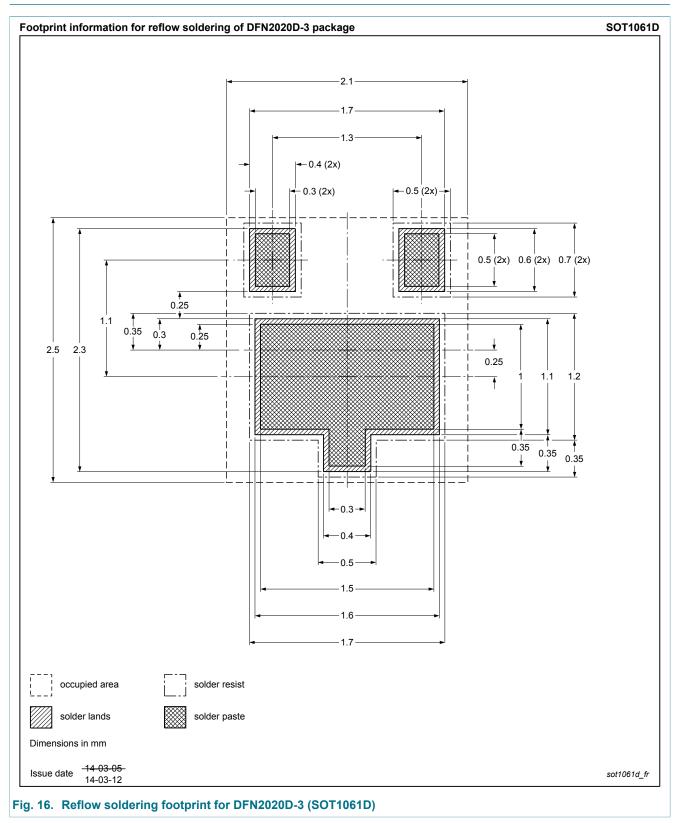
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMEG4010CPAS v.3	20151006	Product data sheet	-	PMEG4010CPAS v.2			
Modifications:	 layout correction 						
PMEG4010CPAS v.2	20150120	Product data sheet	-	PMEG4010CPAS v.1			
PMEG4010CPAS v.1	20141210	Preliminary data sheet	-	-			

40 V, 1 A low VF dual MEGA Schottky barrier rectifier

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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40 V, 1 A low VF dual MEGA Schottky barrier rectifier

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	9
11.1	Quality information	9
12	Package outline	10
13	Soldering	11
14	Revision history	12
15	Legal information	13
15.1	Data sheet status	13
15.2	Definitions	13
15.3	Disclaimers	13
15.4	Trademarks	14

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